

Preface

This volume is the compilation of the accepted proceedings which were submitted to the 10th European Conference on Silicon Carbide and Related Materials 2014 (ECSCRM2014) held in Grenoble, France, from September 21th to 25th. This conference provided an international scientific forum to 570 researchers and engineers from 29 countries for the exchange of ideas on recent issues in the field of wide bandgap semiconductors, mostly silicon carbide (SiC) but also III-nitrides, diamond and their related materials such as graphene. We hope that the attendees enjoyed this event as much as we enjoyed organizing it.

The attendance to ECSCRM conferences is constantly growing over the years, which is the obvious sign of great improvements obtained recently on every aspect of wide bandgap semiconductor technologies, with the increased participation of industry.

The conference involved 332 abstracts including 13 invited presentations. These contributions covered most of the current research on SiC and related semiconductor materials. The present book contains 243 proceedings distributed among 5 main topics, i.e. SiC growth, Theory and characterization, Processing, Devices and Related materials. We wish to thank all the contributors of this volume (both authors and reviewers) for their efforts to submit and correct high quality papers on time and edition ready.

The success of ECSCRM2014 is the result of the hard work and dedication of many persons. We would like to express our sincere gratitude to Domitille Tricou and Camille Villette for their constant help and support on many organizational aspects, both on site and during the last 2 years. We would also like to thank the local helping teams from LMI, LMGP and Ampere laboratories for their precious technical contribution. The Technical Program committee and the International steering committee are deeply acknowledged for their valuable help and suggestions to make this event be of high scientific quality and as attractive as possible. Sponsors and partners of the conference are also much thanked for their financial support which is essential for making everything going smoothly.

The next conference of this series will be held in 2016 in Chalkidiki, Greece, Chaired by Prof. Efstathios Polychroniadis and Konstantinos Zekentes. We sincerely wish the organizers much success.

Grenoble, January 2015

Didier Chaussende and Gabriel Ferro

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